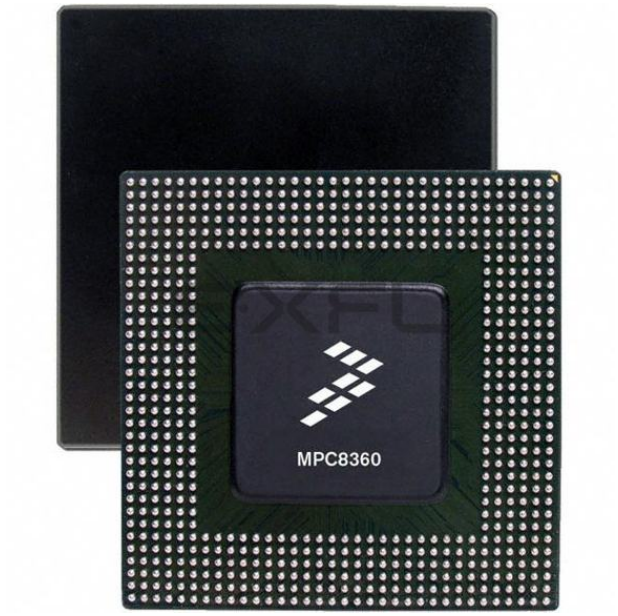

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8360evvalfha

4.1 DC Electrical Characteristics

This table provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the device.

Table 7. CLKIN DC Electrical Characteristics

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	0 V ≤V_{IN} ≤OV_{DD}	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	0 V ≤V_{IN} ≤0.5V or OV_{DD} – 0.5V ≤V_{IN} ≤OV_{DD}	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	0.5 V ≤V_{IN} ≤OV_{DD} – 0.5 V	I_{IN}	—	±100	μA

4.2 AC Electrical Characteristics

The primary clock source for the device can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. This table provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 8. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, USB, security, and 10/100/1000 Ethernet must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

4.3 Gigabit Reference Clock Input Timing

This table provides the Gigabit reference clocks (GTX_CLK125) AC timing specifications.

Table 9. GTX_CLK125 AC Timing Specifications

At recommended operating conditions with LV_{DD} = 2.5 ± 0.125 mV/ 3.3 V ± 165 mV

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
GTX_CLK125 frequency	t_{G125}	—	125	—	MHz	—
GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤V_{IN} ≤OV_{DD})	I_{IN}	—	±10	µA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤V_{OUT} ≤GV_{DD}.

This table provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 17. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM interface when GV_{DD}(typ) = 1.8 V.

Table 18. DDR2 SDRAM Input AC Timing Specifications for GV_{DD}(typ) = 1.8 V

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

This table provides the input AC timing specifications for the DDR SDRAM interface when GV_{DD}(typ) = 2.5 V.

Table 19. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

Table 20. DDR and DDR2 SDRAM Input AC Timing Specifications Mode

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
MDQS—MDQ/MECC input skew per byte	t_{DISKEW}			ps	1, 2
333 MHz		–750	750		
266 MHz		–1125	1125		
200 MHz		–1250	1250		

Notes:
1. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
2. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 ≤n ≤7) or ECC (MECC[{0...7}] if n = 8).

This figure shows the input timing diagram for the DDR controller.

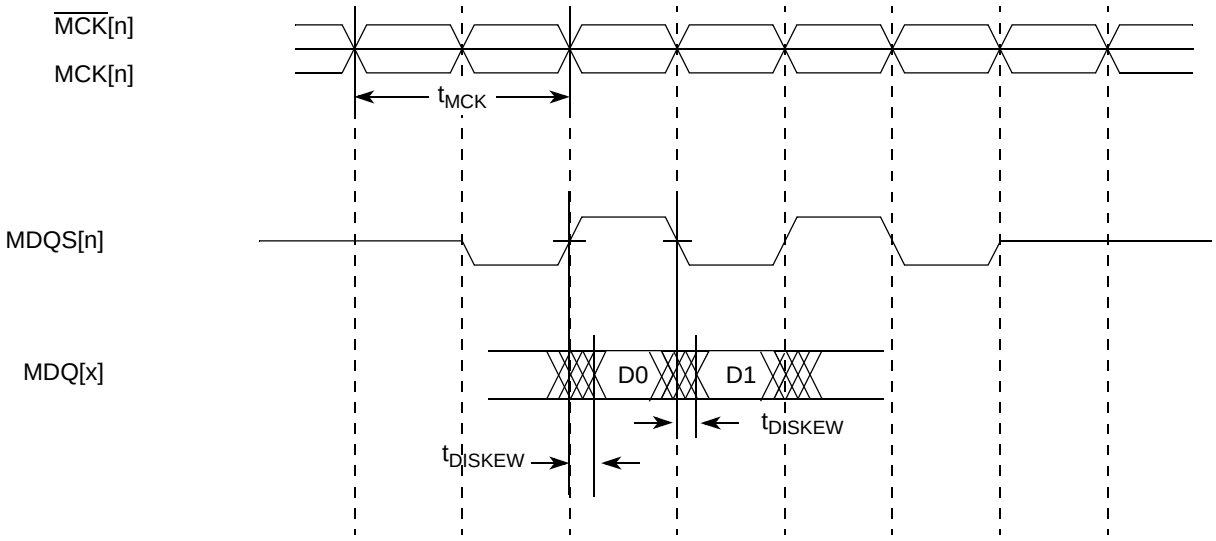

Figure 6. DDR Input Timing Diagram

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 21 and Table 22 provide the output AC timing specifications and measurement conditions for the DDR and DDR2 SDRAM interface.

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t_{AOSKEW}	 –1.0 –1.1 –1.2	 0.2 0.3 0.4	ns	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	 2.1 2.8 3.5	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz—DDR1 266 MHz—DDR2 200 MHz	t_{DDKHAX}	 2.0 2.7 2.8 3.5	—	ns	4
$\overline{\text{MCS}}$(n) output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	 2.1 2.8 3.5	—	ns	4
$\overline{\text{MCS}}$(n) output hold with respect to MCK 333 MHz 266 MHz 200 MHz	t_{DDKHCX}	 2.0 2.7 3.5	—	ns	4
MCK to MDQS	t_{DDKHMH}	–0.8	0.7	ns	5, 9
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 0.7 1.0 1.2	—	ns	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 0.7 1.0 1.2	—	ns	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	7

8.2.1.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

Table 27. GMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{GTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	$t_{GTXH/tGTX}$	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX} t_{GTKHDV}	0.5 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{GTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{GTXF}	—	—	1.0	ns	—
GTX_CLK125 clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $LV_{DD/2}$	t_{G125H}/t_{G125}	45	—	55	%	2

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 signal and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata, t_{GTKHDX} minimum and t_{GTKHDV} maximum are not supported when the GTX_CLK is selected. Refer to Errata *QE_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII transmit AC timing diagram.

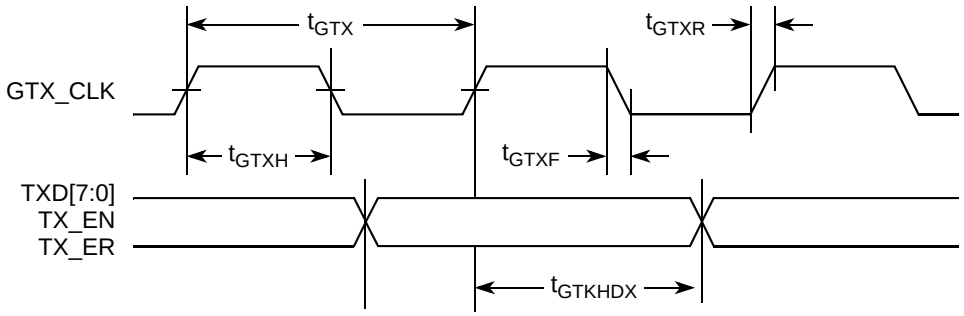

Figure 10. GMII Transmit AC Timing Diagram

8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 33. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns	—
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%	—
GTX_CLK to TBI data TCG[9:0] delay	t_{TTKHDX} t_{TTKHDV}	1.0 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t_{TTXR}	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t_{TTXF}	—	—	1.0	ns	—
GTX_CLK125 reference clock period	t_{G125}	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	45	—	55	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX_CLK125 and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata, t_{TTKHDX} minimum is 0.7 ns for UCC1. Refer to Errata *QE_ENET19* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the TBI transmit AC timing diagram.

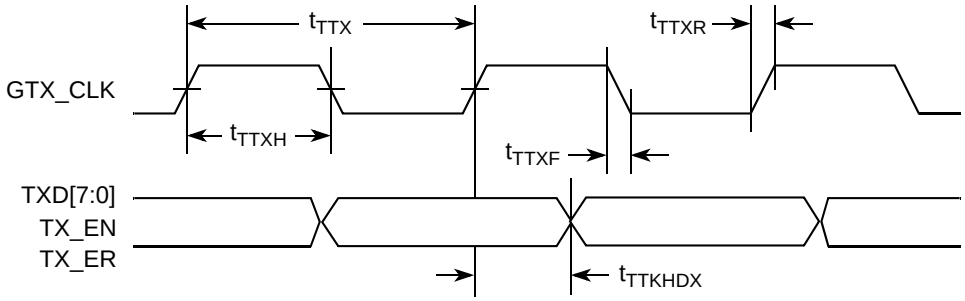

Figure 18. TBI Transmit AC Timing Diagram

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

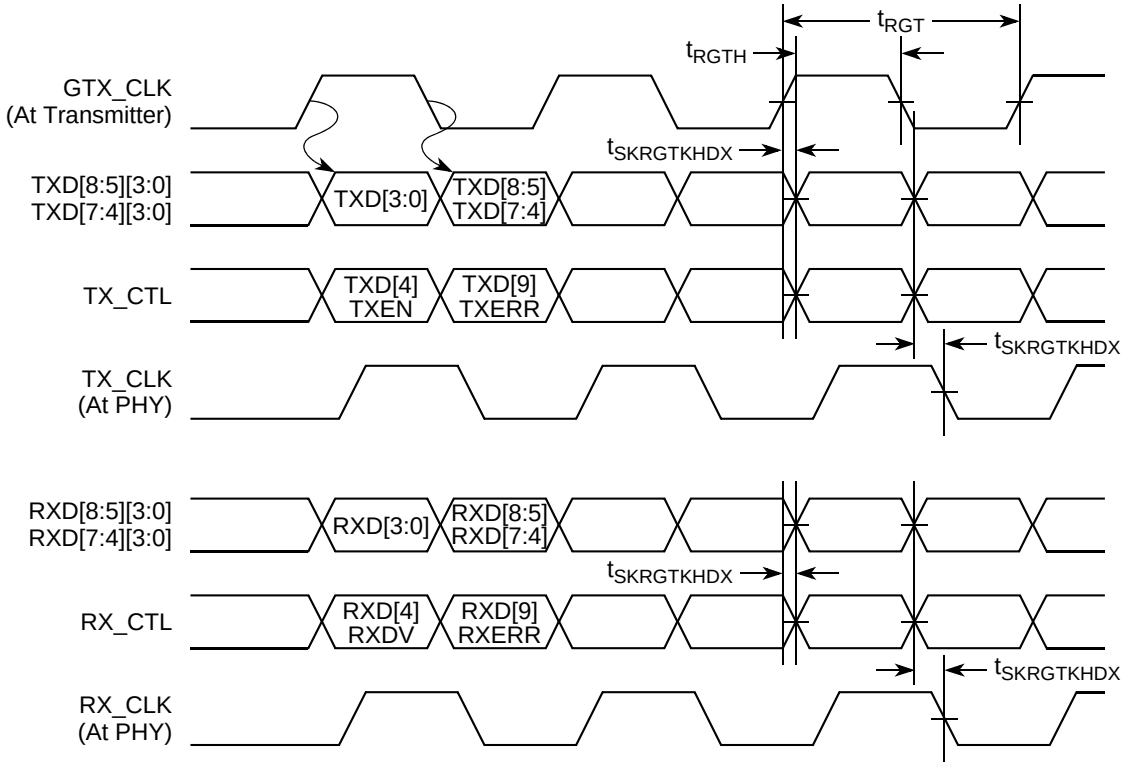

Figure 20. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (10/100/1000 Mbps)— GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	OV_{DD} = Min	2.10	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±10	μA

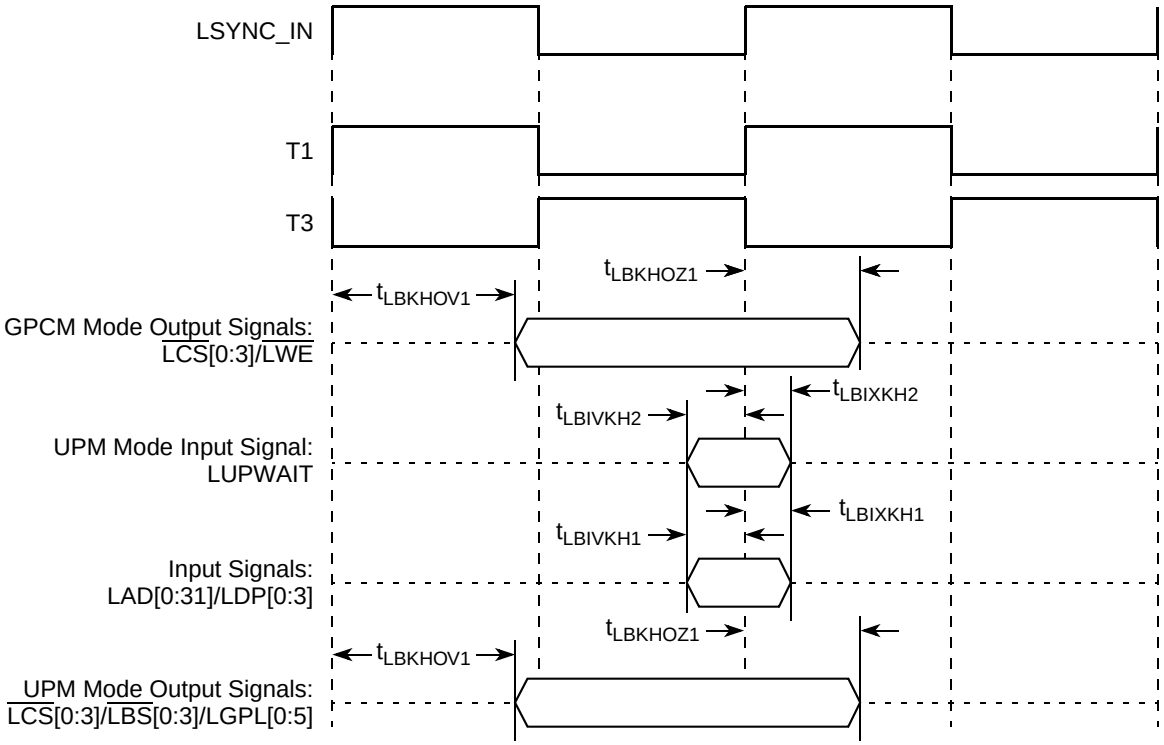

Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

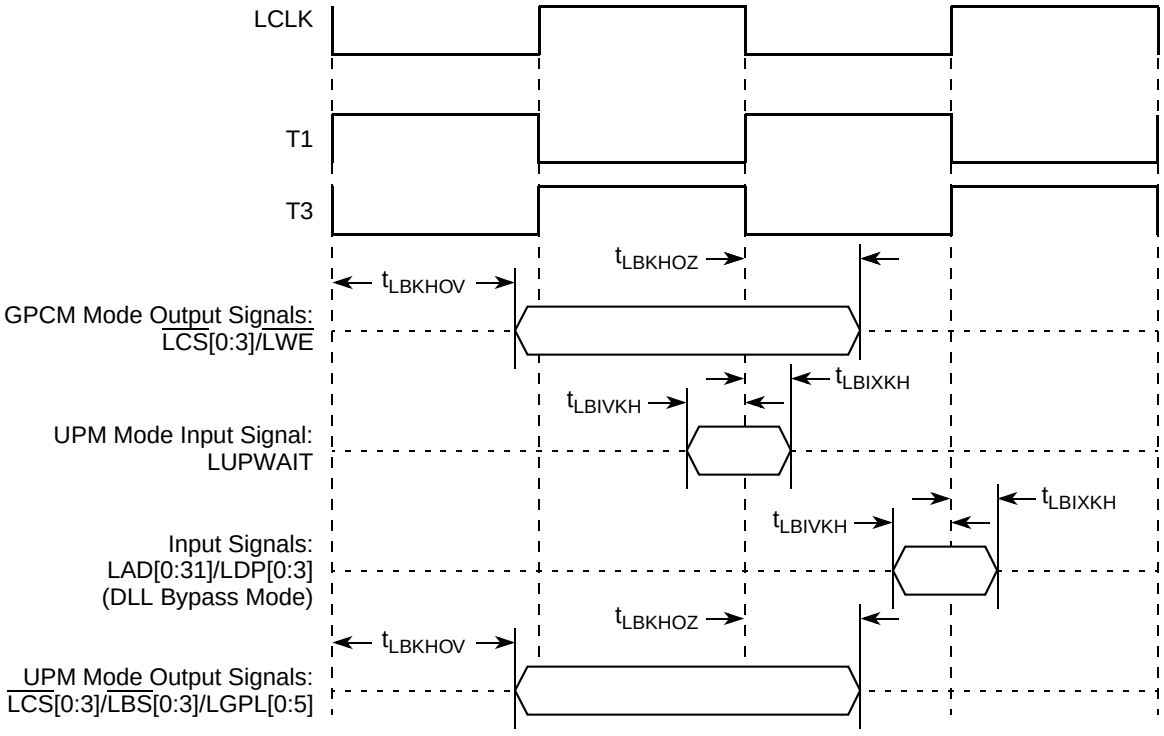

Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

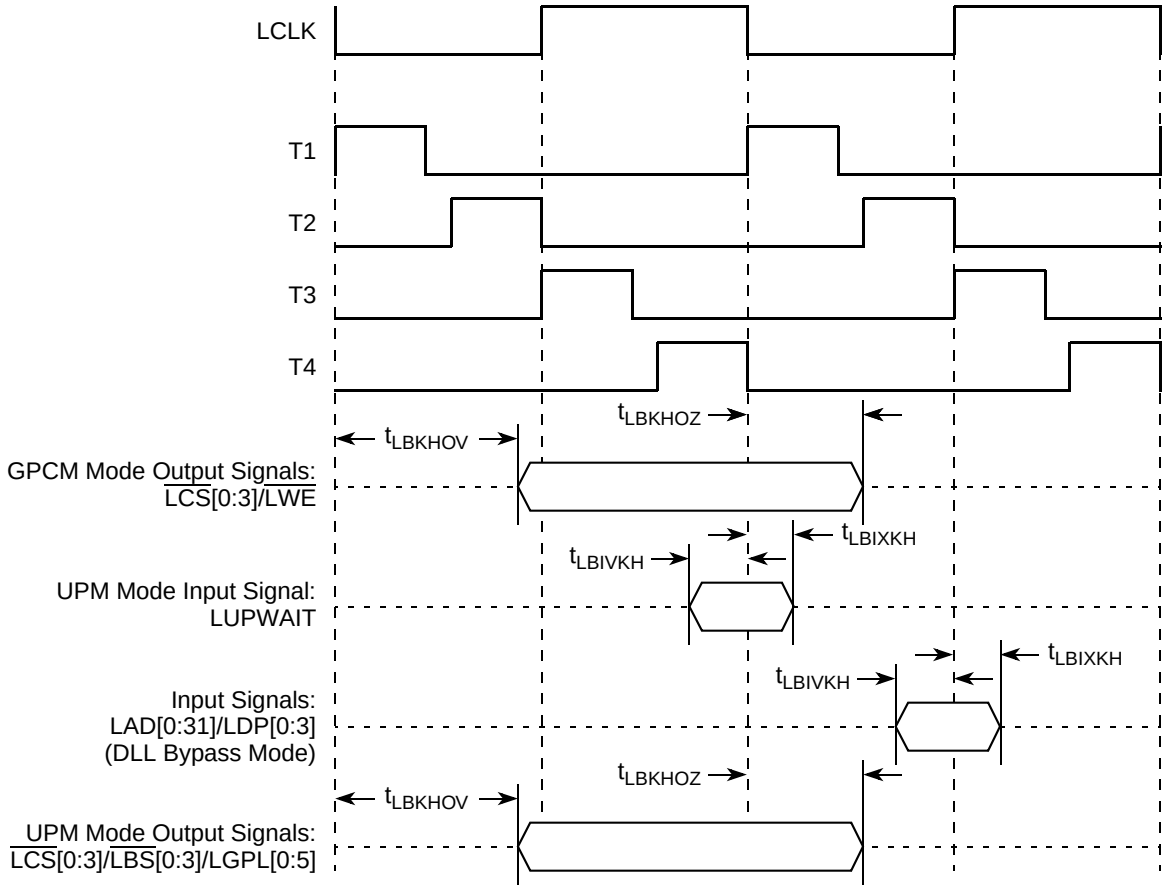

Figure 27. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Bypass Mode)

10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)[1]

At recommended operating conditions (see Table 2).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock duty cycle	t_{JTKHKL}/t_{JTG}	45	55	%	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	—
$\overline{\text{TRST}}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 4	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 10 10	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 2 2	 11 11	ns	5
Output hold times: Boundary-scan data TDO	 t_{JTKLDX} t_{JTKLOX}	 2 2	 — —	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

11.2 I²C AC Electrical Specifications

This table provides the AC timing parameters for the I²C interface of the device.

Table 45. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 44).

Parameter	Symbol[1]	Min	Max	Unit	Note
SCL clock frequency	f_{I2C}	0	400	kHz	2
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	—
High period of the SCL clock	t_{I2CH}	0.6	—	μs	—
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	—
Data setup time	t_{I2DVKH}	100	—	ns	3
Data hold time: CBUS compatible masters I²C bus devices	t_{I2DXKL}	 — 0[2]	 — 0.9[3]	μs	—
Rise time of both SDA and SCL signals	t_{I2CR}	20 + 0.1 C_b[4]	300	ns	—
Fall time of both SDA and SCL signals	t_{I2CF}	20 + 0.1 C_b[4]	300	ns	—
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs	—
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	0.1 × OV_{DD}	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	0.2 × OV_{DD}	—	V	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} min of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

13.2 Timers AC Timing Specifications

This table provides the timer input and output AC timing specifications.

Table 50. Timers Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timers inputs and outputs are asynchronous to any visible clock. Timers outputs should be synchronized before use by any external synchronous logic. Timers inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

This figure provides the AC test load for the timers.

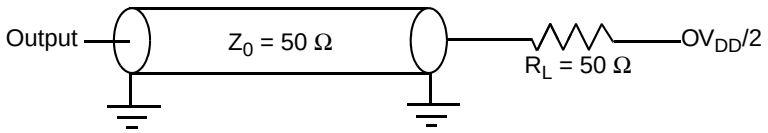

Figure 39. Timers AC Test Load

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the MPC8360E/58E.

14.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the device GPIO.

Table 51. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA	—

Note:
1. This specification applies when operating from 3.3-V supply.

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock high impedance	t_{HIKHOX}	-0.5	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	8.5	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	1.4	—	ns
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 63. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

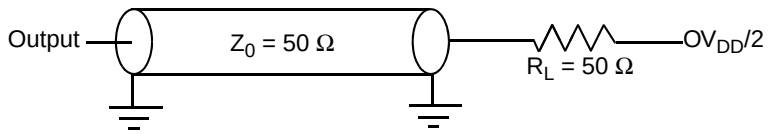

Figure 49. AC Test Load

20.2 Mechanical Dimensions of the TBGA Package

This figure depicts the mechanical dimensions and bottom surface nomenclature of the device, 740-TBGA package.

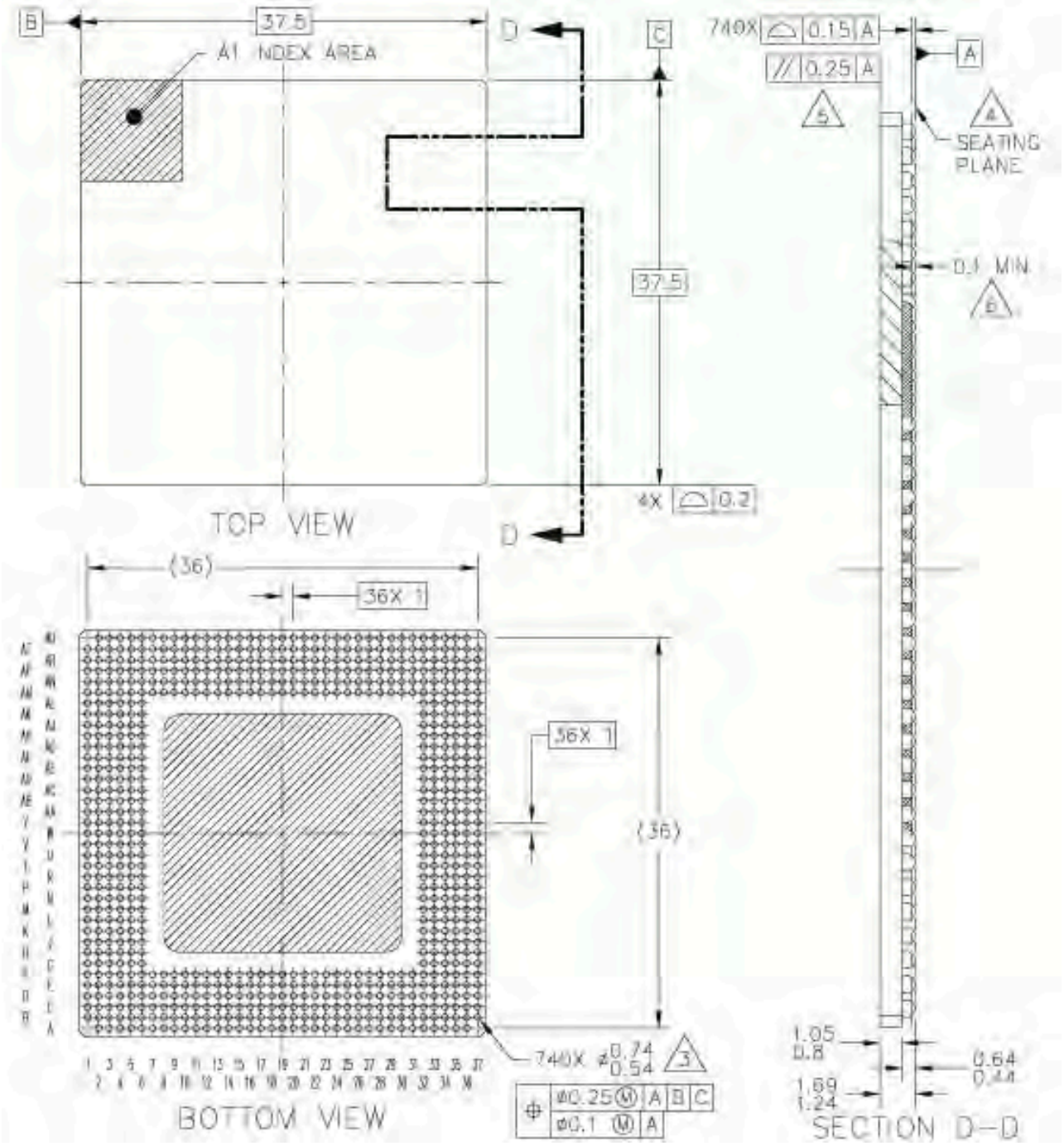

Figure 53. Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package

Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$LV_{DD}0$	D5, D6	Power for UCC1 Ethernet interface (2.5 V, 3.3 V)	$LV_{DD}0$	—
$LV_{DD}1$	C17, D16	Power for UCC2 Ethernet interface option 1 (2.5 V, 3.3 V)	$LV_{DD}1$	9
$LV_{DD}2$	B18, E21	Power for UCC2 Ethernet interface option 2 (2.5 V, 3.3 V)	$LV_{DD}2$	9
V_{DD}	C36, D29, D35, E16, F9, F12, F15, F17, F18, F20, F21, F23, F25, F26, F29, F31, F32, F33, G6, J6, K32, M32, N6, P33, R6, R32, U32, V6, Y5, Y32, AB6, AB33, AD6, AF32, AK6, AL6, AM7, AM9, AM10, AM11, AM12, AM13, AM14, AM15, AM18, AM21, AM25, AM28, AM32, AN15, AN21, AN26, AU9, AU17	Power for core (1.2 V)	V_{DD}	—
OV_{DD}	A10, B9, B15, B32, C1, C12, C22, C29, D24, E3, E10, E27, G4, H35, J1, J35, K2, M4, N3, N34, R2, R37, T36, U2, U33, V4, V34, W3, Y35, Y37, AA1, AA36, AB2, AB34	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV_{DD}	—
MVREF1	AN20	I	DDR reference voltage	—
MVREF2	AU32	I	DDR reference voltage	—
SPARE1	B11	I/O	OV_{DD}	8
SPARE3	AH32	—	GV_{DD}	8
SPARE4	AU18	—	GV_{DD}	7
SPARE5	AP1	—	GV_{DD}	8

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE_PB[0:27]	AE2, AE1, AD5, AD3, AD2, AC6, AC5, AC4, AC2, AC1, AB5, AB4, AB3, AB1, AA6, AA4, AA2, Y6, Y4, Y3, Y2, Y1, W6, W5, W2, V5, V3, V2	I/O	OV_{DD}	—
CE_PC[0:1]	V1, U6	I/O	OV_{DD}	
CE_PC[2:3]	C16, A15	I/O	$LV_{DD}1$	—
CE_PC[4:6]	U4, U3, T6	I/O	OV_{DD}	—
CE_PC[7]	C19	I/O	$LV_{DD}2$	—
CE_PC[8:9]	A4, C5	I/O	$LV_{DD}0$	—
CE_PC[10:30]	T5, T4, T2, T1, R5, R3, R1, C11, D12, F13, B10, C10, E12, A9, B8, D10, A14, E15, B14, D15, AH2	I/O	OV_{DD}	—
CE_PD[0:27]	E11, D9, C8, F11, A7, E9, C7, A6, F10, B6, D7, E8, B5, A5, C2, E4, F5, B1, D2, G5, D1, E2, H6, F3, E1, F2, G3, H4	I/O	OV_{DD}	—
CE_PE[0:31]	K3, J2, F1, G2, J5, H3, G1, H2, K6, J3, K5, K4, L6, P6, P4, P3, P1, N4, N5, N2, N1, M2, M3, M5, M6, L1, L2, L4, E14, C13, C14, B13	I/O	OV_{DD}	—
CE_PF[0:3]	F14, D13, A12, A11	I/O	OV_{DD}	—
Clocks				
PCI_CLK_OUT[0]/CE_PF[26]	B22	I/O	$LV_{DD}2$	—
PCI_CLK_OUT[1:2]/CE_PF[27:28]	D22, A23	I/O	OV_{DD}	—
CLKIN	E37	I	OV_{DD}	—
PCI_CLOCK/PCI_SYNC_IN	M36	I	OV_{DD}	—
PCI_SYNC_OUT/CE_PF[29]	D37	I/O	OV_{DD}	3
JTAG				
TCK	K33	I	OV_{DD}	—
TDI	K34	I	OV_{DD}	4
TDO	H37	O	OV_{DD}	3
TMS	J36	I	OV_{DD}	4
$\overline{\text{TRST}}$	L32	I	OV_{DD}	4
Test				
TEST	L35	I	OV_{DD}	7
$\overline{\text{TEST\_SEL}}$	AU34	I	GV_{DD}	10
PMC				
$\overline{\text{QUIESCE}}$	B36	O	OV_{DD}	—
System Control				

Table 70. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in this table.

Table 71. System PLL VCO Divider

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

The system VCO frequency is derived from the following equations:

- *csb_clk* = {PCI_SYNC_IN × (1 + CFG_CLKIN_DIV)} × SPMF
- System VCO Frequency = *csb_clk* × VCO divider (if both RCWL[DDRCM] and RCWL[LBCM] are cleared) OR
- System VCO frequency = 2 × *csb_clk* × VCO divider (if either RCWL[DDRCM] or RCWL[LBCM] are set).

As described in Section 21, "Clocking," the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). This table shows the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 72. CSB Frequency Options

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk*: Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2:1				133
Low	0011	3:1			100	200
Low	0100	4:1		100	133	266
Low	0101	5:1		125	166	333

21.3 QUICC Engine Block PLL Configuration

The QUICC Engine block PLL is controlled by the RCWL[CEPMF], RCWL[CEPDF], and RCWL[CEVCOD] parameters. This table shows the multiplication factor encodings for the QUICC Engine block PLL.

Table 74. QUICC Engine Block PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000	0	× 16
00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001	0	× 9
01010	0	× 10
01011	0	× 11
01100	0	× 12
01101	0	× 13
01110	0	× 14
01111	0	× 15
10000	0	× 16
10001	0	× 17
10010	0	× 18
10011	0	× 19
10100	0	× 20
10101	0	× 21
10110	0	× 22
10111	0	× 23
11000	0	× 24
11001	0	× 25
11010	0	× 26
11011	0	× 27
11100	0	× 28

This figure shows the PLL power supply filter circuit.

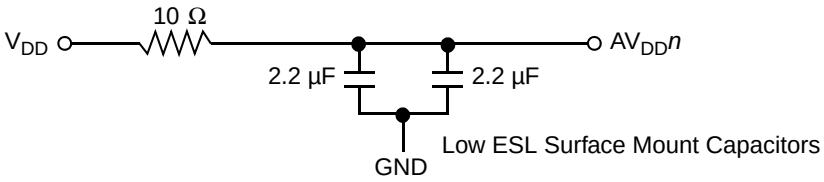

Figure 56. PLL Power Supply Filter Circuit

23.3 Decoupling Recommendations

Due to large address and data buses as well as high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pins of the device. These decoupling capacitors should receive their power from separate V_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

Additionally, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

23.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to OV_{DD}, GV_{DD}, or LV_{DD} as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD}, GV_{DD}, LV_{DD}, OV_{DD}, and GND pins of the device.

23.5 Output Buffer DC Impedance

The device drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 57). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

23.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins including I^2C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24 Ordering Information

24.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the MPC8360E/58E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. Additionally to the processor frequency, the part numbering scheme also includes an application modifier, which may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 80. Part Numbering Nomenclature[1]

MPC	***nnnn***	***e***	***t***	***pp***	***aa***	***a***	***a***	***A***
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature Range**	**Package[2]**	**Processor Frequency[3]**	**Platform Frequency**	**QUICC Engine Frequency**	**Die Revision**
MPC	8358	Blank = not included E = included	Blank = 0° C T_A to 105° C T_J C= –40° C T_A to 105° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AD = 266 MHz AG = 400 MHz	D = 266 MHz	E = 300 MHz G = 400 MHz	A = rev. 2.1 silicon
	8360				e300 core speed AG = 400 MHz AJ = 533 MHz AL = 667 MHz	D = 266 MHz F = 333 MHz	G = 400 MHz H = 500 MHz	A = rev. 2.1 silicon
MPC (rev. 2.0 silicon only)	8360	Blank = not included E = included	0° C T_A to 70° C T_J	ZU = TBGA VV = TBGA (no lead)	e300 core speed AH = 500 MHz AL = 667 MHz	F = 333 MHz	G = 400 MHz H = 500 MHz	—

Notes:

1. Not all processor, platform, and QUICC Engine block frequency combinations are supported. For available frequency combinations, contact your local Freescale sales office or authorized distributor.
2. See Section 20, "Package and Pin Listings," for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.

This table shows the SVR settings by device and package type.

Table 81. SVR Settings

Device	Package	SVR (Rev. 2.0)	SVR (Rev. 2.1)
MPC8360E	TBGA	0x8048_0020	0x8048_0021
MPC8360	TBGA	0x8049_0020	0x8049_0021